Investor Presentation

August 2018

Weebit nano

WEEBIT NANO AT A GLANCE

Listed on the ASX in August 2016

Targeting the non-volatile memory market estimated at > USD$60B

R&D and HQ in Israel, R&D partnership with CEA-Leti, France

Business & Tech partners – CEA-Leti France & Rice University, USA

Developing next-gen solution based on Silicon Oxide (SiOx) ReRAM
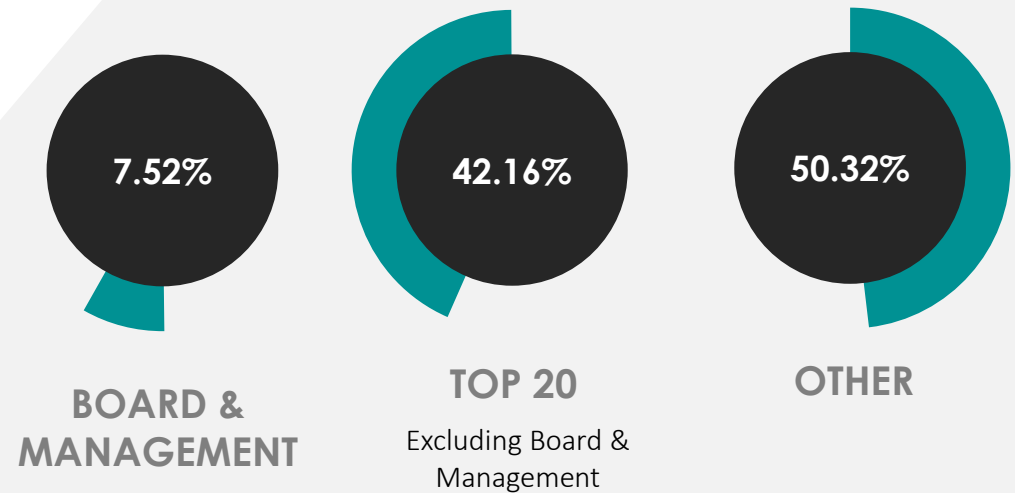
Patents Registered in the USA

Weebitnano
The Future Memory

SHARE INFORMATION

CAPITAL STRUCTURE

01	ASX Code: WBT
02	Share price: 5.1c[1]
03	Shares on issue: 1451m[1]
04	Options: 141m[1&2]
05	Market cap: A$74.02m[1]
06	Cash: A$3.36m[3]

1. As of 28 August 2018
2. Including performance shares
3. As of 30 June 2018

SHAREHOLDING BREAKDOWN

7.52%

BOARD & MANAGEMENT

42.16%

TOP 20
Excluding Board & Management

50.32%

OTHER

Weebitnano
The Future Memory

LEADERSHIP TEAM

EXECUTIVE DIRECTOR

Yoav Nissan-Cohen

PhD. in Applied Physics, focus on SiOx memories

CEO of Tower Semiconductor for 9 years

Board member, Saifun Semiconductor (NROM Flash)

CHAIRMAN

David Perlmutter

Ex-Intel EVP IEEE Fellow

Led Intel into the Data Center

Brought to Market: Centrino™ mobile technology

CEO

Coby Hanoch

Extensive management and sales experience

38 years in the semiconductor domain

Heavily involved in Verisity and Jasper acquisitions

CTO

Amir Regev

Two decades in Semiconductor engineering

45nm NOR Flash Technology Development at Micron

Was part of Automotive division at Intel

CFO

Alla Felder

20 Years CPA experience

Senior Manager at PWC Israel

Active Board member of multiple companies in TASE and NASDAQ

NON-EXEC/ADVISORY TEAM

DIRECTOR

Fred Bart

Chairman and major shareholder of Electro Optics Systems (EOS)

Chairman of Audio Pixels (AKP)

Owns a wide variety of companies worldwide

DIRECTOR

Ashley Krongold

15 years in Investment Banking

Founding member of Investec Bank Australia

Founding General Partner, OurCrowd

DIRECTOR

Yossi Keret

Extensive management and financial experience

Led the financial teams at a number of publicly traded international companies

Strong experience in equity raisings for public companies

INVENTOR

Prof. James Tour

Scientist of the Year 2013 R&D magazine

Inducted to the National Academy of inventors

Feynman prize in Nano science

5

WEEBIT RERAM TECHNOLOGY

Next generation memory technology

Faster and more efficient than flash memory

Prototype 40nm 1Mb array achieved – comparable with current embedded memory technology

Key differentiator: WBT uses silicon oxide – the most commonly used material in the semiconductor industry

Silicon oxide enables lower cost and shorter time to market

RERAM VS. FLASH

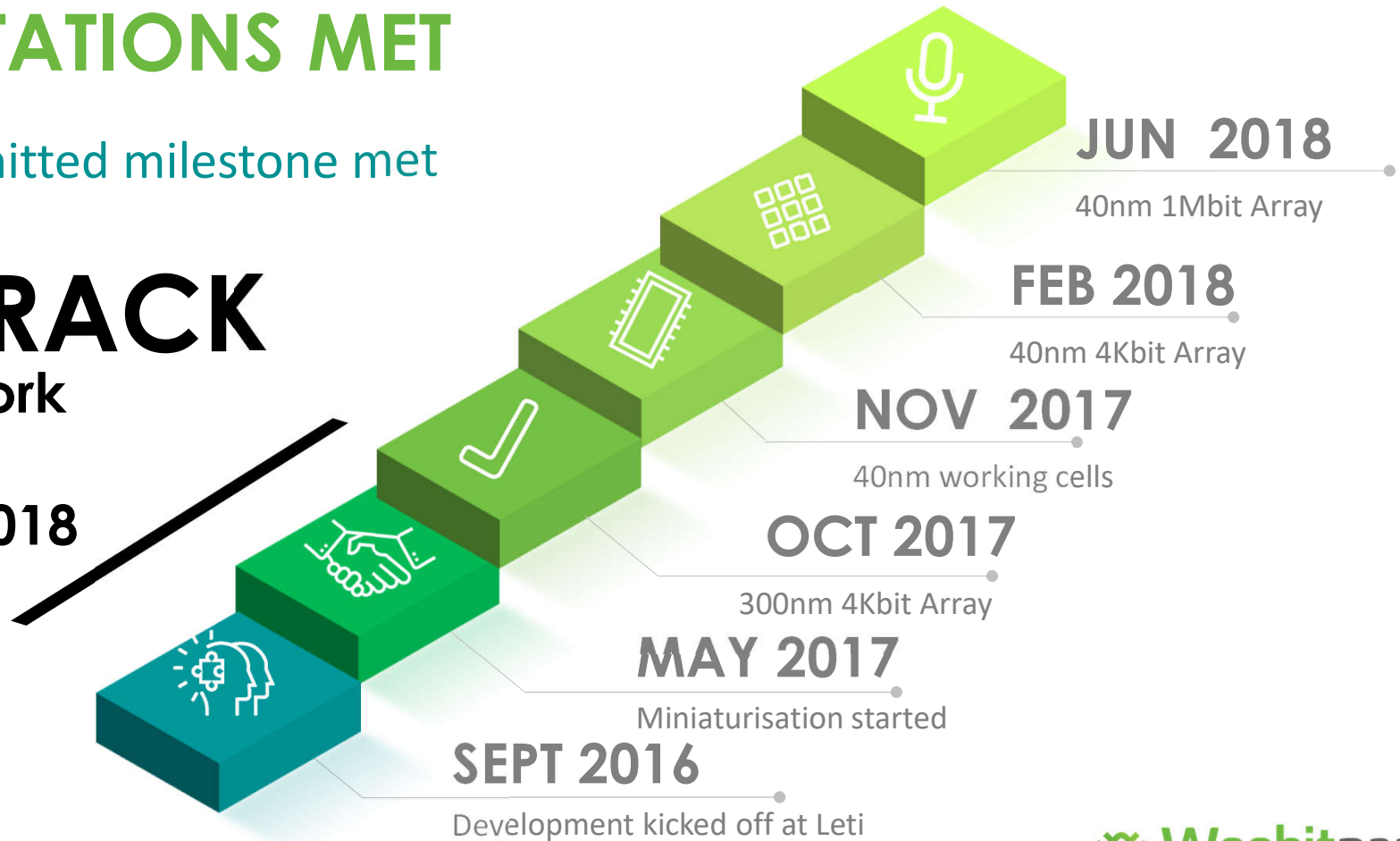The parameters needed for the next generation memory solution are:

	Flash (3D-NAND)		Weebit's ReRAM	
Speed	Does not provide any speed improvement for tomorrow's needs	✗	~1000X faster programming and read operations	✓
Energy Efficiency	No power improvement per bit, consumes higher energy	✗	~1000X more energy efficient by low voltage and fast write	✓
Manufacturability	Very challenging manufacturing process, not compatible with standard logic process (very difficult to embed)	✗	Simple process, utilises standard material and machinery – compatible with standard logic process	✓
Density	Provides increased capacity for the near future	✓	Scalability allows higher future density	✓
Reliability	High error rate and limited endurance	✗	10-100X higher endurance	✓

Weebitnano
The Future Memory

EXPECTATIONS MET

Every committed milestone met

ON TRACK
to start work
on 28nm
by end-2018

JUN 2018
40nm 1Mbit Array

FEB 2018
40nm 4Kbit Array

NOV 2017
40nm working cells

OCT 2017
300nm 4Kbit Array

MAY 2017
Miniaturisation started
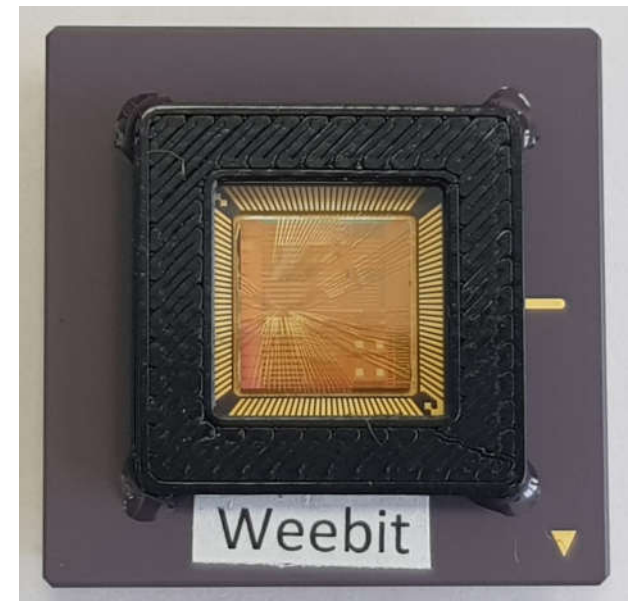
SEPT 2016
Development kicked off at Leti
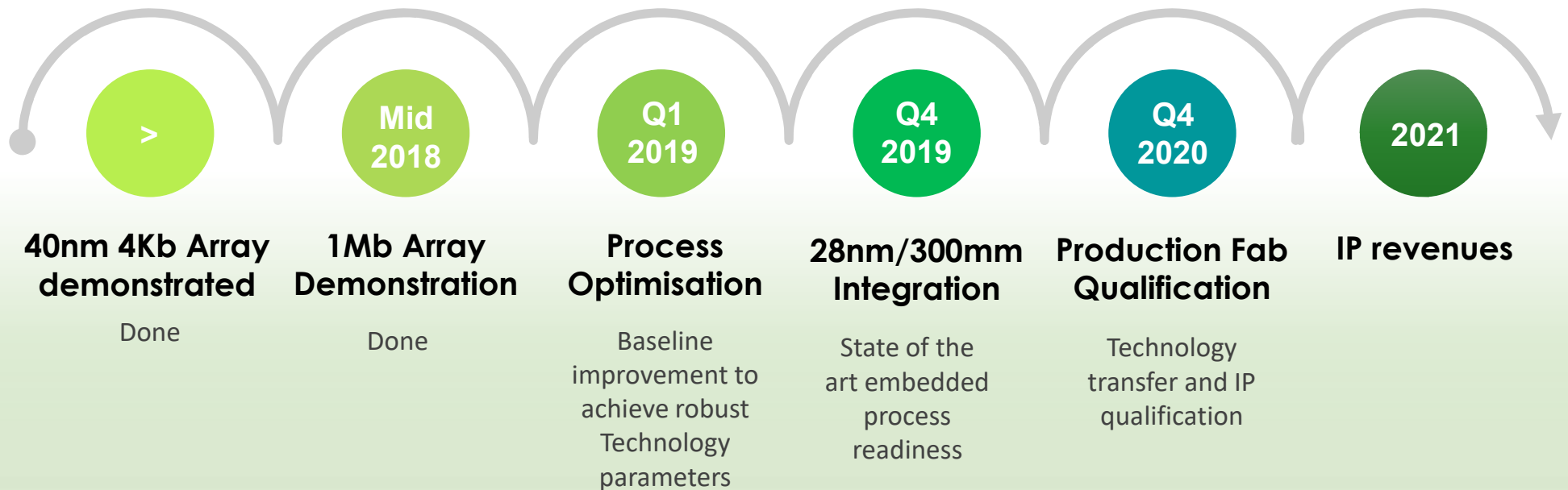
8

Weebitnano
The Future Memory

FIRST MEMORY CHIP PACKAGED

Moving closer to commercialisation

- First packages of SiOx 1Mb 40nm memory chips now ready

  Memory chips are in the form of existing memory chips being used by customers in phones, PCs or storage devices

- Enables additional testing as the company moves closer to commercialisation

- Technology can now be shipped to potential partners for evaluation

  Will assist in potential commercial partnership discussions

- Universities can begin neuromorphic computing research (used for Artificial Intelligence) using WBT's technology

Weebit

Weebitnano
The Future Memory

STEPS TOWARDS COMMERCIALISATION

>	Mid 2018	Q1 2019	Q4 2019	Q4 2020	2021
40nm 4Kb Array demonstrated	**1Mb Array Demonstration**	**Process Optimisation**	**28nm/300mm Integration**	**Production Fab Qualification**	**IP revenues**
Done	Done	Baseline improvement to achieve robust Technology parameters	State of the art embedded process readiness	Technology transfer and IP qualification	

* Timeline refers to calendar year

Weebitnano
The Future Memory

ALLIANCE WITH CEA – LETI*

A real partnership, with ideal mix of expertise, innovation and flexibility

France-based research institute for electronics and information technologies
Leti assists companies to bridge the gap between research and manufacturing

FROM PROTOTYPES TO PRODUCTION
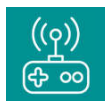Proven international track record in moving from R&D to production
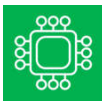
MEMORY EXPERTISE
Over 10 years of experience in memory technology development

NANOTECHNOLOGY SPECIALIST
State of the art industrial tools

MANUFACTURING ALLIANCES
Over 330 industrial partners

INNOVATION HUB
60+ start-ups in semiconductor, architectures or software

COLLABORATION
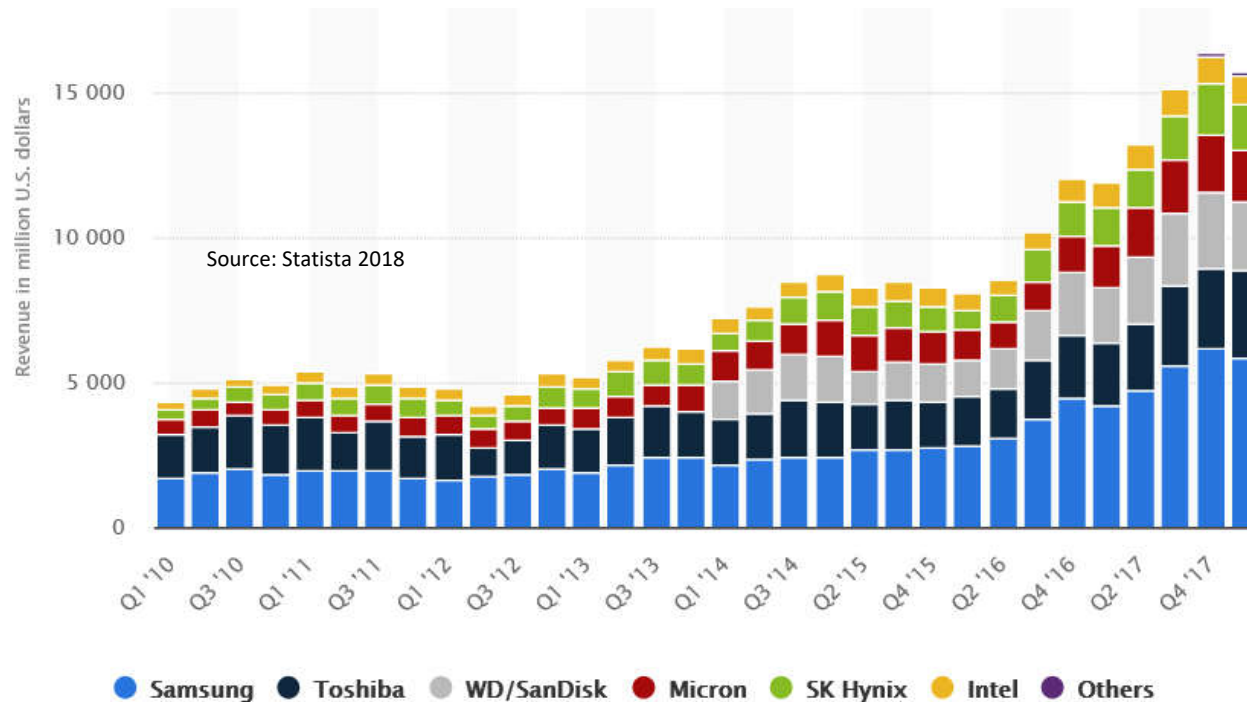Working on 40nm SiOx development since September 2016

CUSTOMERS
Intel, ST Microelectronics, Global foundries

leti cea tech

Weebitnano
The Future Memory

FLASH MARKET OVERVIEW

Quarterly NAND Flash manufacturers' revenue worldwide

Source: Statista 2018

- **Large market experiencing exponential growth**

- **Over US$60B/year**

ReRAM: FORECAST FOR EXPONENTIAL GROWTH IN MARKET VALUE

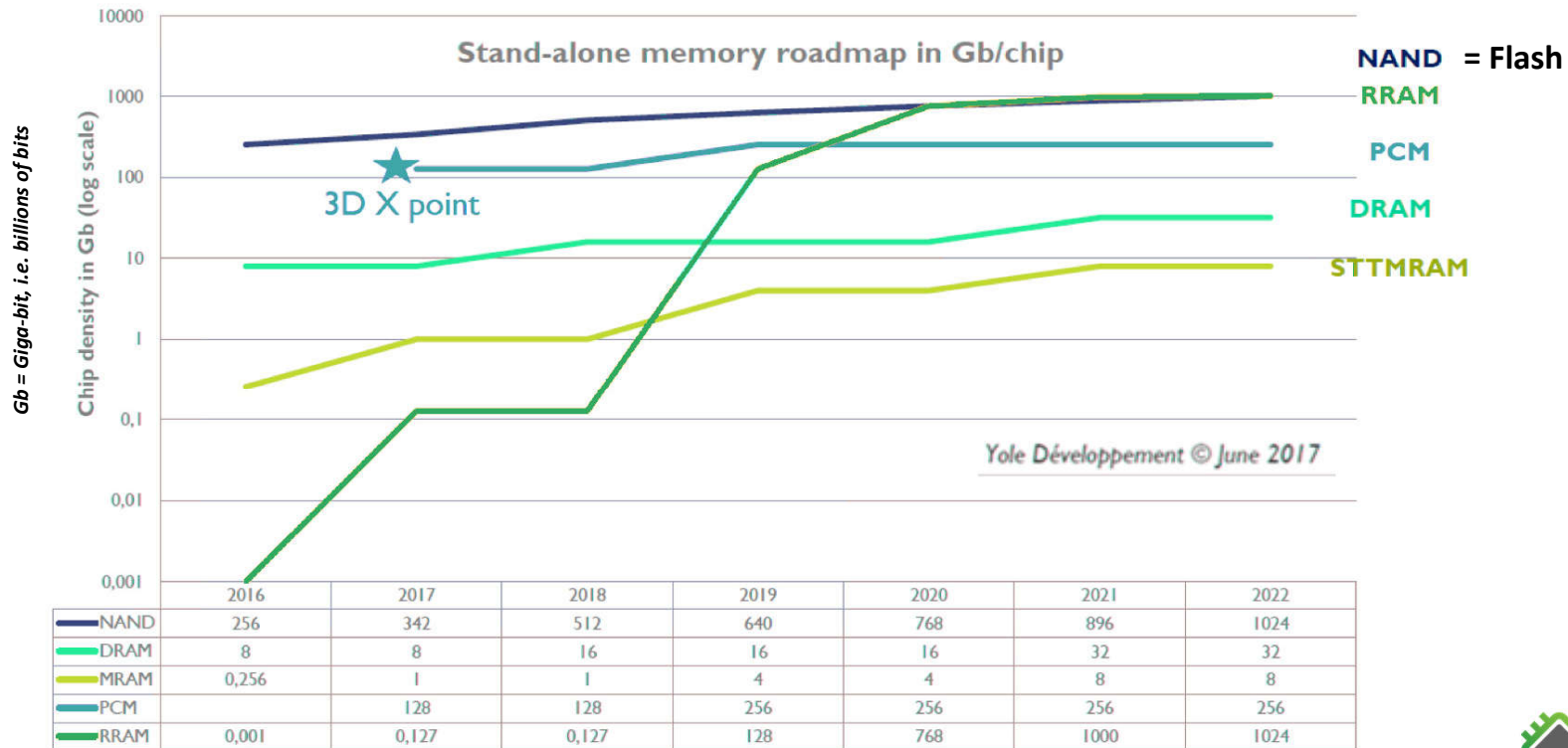**Emerging Non-Volatile Memory Forecast by Technology (in $M)**

Yole Développement © June 2017

	2016	2017	2018	2019	2020	2021	2022	CAGR 2016-2022
TOTAL in $M	$51	$161	$361	$898	$1,523	$2,581	$3,891	106%
PCM	$-	$90	$162	$413	$721	$1,077	$1,409	0%
RRAM	$16	$28	$132	$365	$561	$1,010	$1,727	119%
MRAM/STT MRAM	$35	$43	$66	$120	$242	$493	$754	67%
% emerging NVM vs total memory market	0.1%	0.2%	0.4%	1.0%	1.6%	2.7%	3.9%	

- Emerging memory technologies forecast for significant growth

- ReRAM technology expected to be the fastest growing emerging memory technology with a CAGR of 119%

- ReRAM forecast growth due to competitive cost/performance in both storage class memory and mass storage applications

Weebitnano
The Future Memory

13

RERAM DENSITY EXPECTED TO MATCH FLASH

Highest capacity memory chips best address Storage Class Memory

Stand-alone memory roadmap in Gb/chip

Gb = Giga-bit, i.e. billions of bits

Chip density in Gb (log scale)

3D X point

NAND = Flash
RRAM
PCM
DRAM
STTMRAM

Yole Développement © June 2017

	2016	2017	2018	2019	2020	2021	2022
NAND	256	342	512	640	768	896	1024
DRAM	8	8	16	16	16	32	32
MRAM	0,256	1	1	4	4	8	8
PCM		128	128	256	256	256	256
RRAM	0,001	0,127	0,127	128	768	1000	1024

Weebitnano
The Future Memory

NEUROMORPHIC COMPUTATION

ReRAM well positioned for significant growth in Artificial Intelligence

- ReRAM's operation mimics the **biological computation at the synaptic level**

  - Physical similarities lead to functional similarities

  - Combines memory and processing units using synapse and neuron like cells

  - **ReRAM for AI is significantly more energy efficient than today's data centres, and significantly smaller**

- ReRAM is therefore very well placed to capitalise on the emergence of AI capabilities
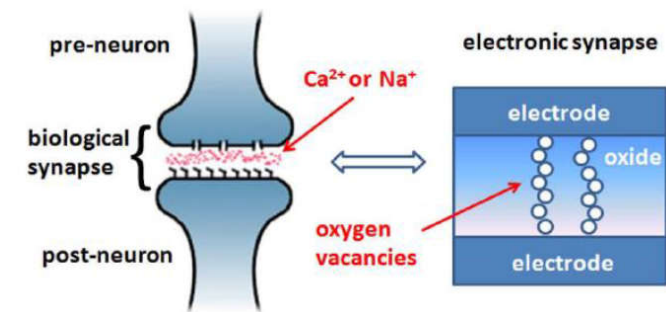
Ions migration leads to resistivity modulation

ReRAM technology enables brain-inspired AI systems

WEEBIT'S COMPETITIVE ADVANTAGE

Speed to market is a significant competitive advantage

- Weebit's ReRAM is based on standard Silicon-Oxide (SiOx) – the material used in the Semiconductor industry for decades

- Doesn't require special tools or processes – easy & fast implementation in any semiconductor fab

- Enables achieving high yields (working parts) faster – directly translates into profits

*"Compared to other competing technologies, it **(Silicon Oxide) offers higher stability, greater resistance contrast, ease of process integration,** and the potential to minimise the requirement for cell selector elements. While there remain some challenges ahead to fully realise SiOx-based ReRAM memory chips or neuromorphic systems, silicon oxide is rapidly emerging as one of, if not **the most, suitable contenders in the race to exploit resistance-switching technologies."***

Adnan Mehonic et al., Advanced Materials Progress Report, 2018

Weebitnano
The Future Memory

16

KEY PRIORITIES FOR NEXT 12 MONTHS

TECHNICAL

- Bring the technology to production-level requirements

- Start working on 28nm technology

BUSINESS

- Sign first cooperation agreement with a key industry player in Q4 2018

Weebitnano
The Future Memory

DISCLAIMER

This presentation contains certain statements that constitute forward-looking statements. Examples of such statements include, but are not limited to, statements regarding the design, scope, initiation, conduct and results of our research and development programs; our plans and objectives for future operations; and the potential benefits of our products and research technologies. In some cases, forward-looking statements can be identified by the use of terminology such as "may," "will," "expects," "plans," "anticipates," "estimates," "potential" or "continue" or the negative thereof or other comparable terminology. These statements involve a number of risks and uncertainties that could cause actual results and the timing of events to differ materially from those anticipated by these forward-looking statements. These risks and uncertainties include a variety of factors, some of which are beyond our control. All forward-looking statements and reasons why actual results may differ are based on information available to us when initially made, and we assume no obligation to update these forward-looking statements or reasons why actual results might differ or the information set forth herein.

In addition, we do not make any representations or warranties, express or implied, with regard to the information included in this presentation of any other related document or information disclosed or furnished in connection thereto, including, without limitation, with respect to the accuracy, reliability, completeness or its sufficiency for any particular purpose. This information is proprietary and confidential of Weebit and is provided on a confidential basis and may not be disclosed or used without our prior written consent. You acknowledge that the disclosure and use of the information may be further prohibited under applicable securities or other laws.

This presentation is made for informational purposes only and does not constitute an offer to sell
any interest in Weebit not does it form the basis of any contract or agreement between the parties.

Third party data

This presentation includes or is otherwise based on information obtained from publicly available information, such as Statistica 2018, Yole Développement June 2017 and Advanced Materials Progress Report, 2018; and (iii) other information publicly released by corporations and government departments. Weebit has not independently verified or audited this information or any information. Accordingly, the accuracy and completeness of such information is not guaranteed. This data has been accurately reproduced and, as far as Weebit is aware, no facts have been omitted that would render the information provided inaccurate or misleading. Investors should note that market data is inherently predictive and subject to uncertainty and is not necessarily reflective of actual market, industry and macroeconomic conditions. Specifically, there is no assurance that any of the forecasts or projections will be achieved. Forecasts and projections involve risks and uncertainties and are subject to change based on various factors, including those discussed above.

THANK YOU

Weebitnano
The Future Memory